SiSA24DN

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Vishay Siliconix

RoHS

COMPLIANT HALOGEN

FREE

N-Channel 25 V (D-S) MOSFET



PRODUCT SUMMARY V_{DS} (V) 25 $R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V 0.00140 $R_{DS(on)}$ max. ($\overline{\Omega}$) at V_{GS} = 4.5 V 0.00240 Qg typ. (nC) 17.2 60 a, g I_D (A) Configuration Single

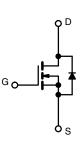
FEATURES

TrenchFET[®] Gen IV power MOSFET

- Optimized Q_g , Q_{gd} , and Q_{gd}/Q_{gs} ratio reduces switching related power loss
- 100 % R_a and UIS tested
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Synchronous rectification
- High power density DC/DC
- Synchronous buck converter
- Load switching



N-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK 1212-8 Single
Lead (Pb)-free and halogen-free	SiSA24DN-T1-GE3

ABSOLUTE MAXIMUM RATING	S (T _A = 25 °C, u	inless other	wise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	25	V	
Gate-source voltage		V _{GS}	+20 / -16	V	
	T _C = 25 °C		60 ^a		
Continuous drain current (T _J = 150 °C)	T _C = 70 °C		60 ^a	1	
	T _A = 25 °C	I _D	38.3 ^{b, c}	1	
	T _A = 70 °C	1	30.8 ^{b, c}		
Pulsed drain current (t = 100 µs)		I _{DM}	150	A	
	T _C = 25 °C		47.2	1	
Continuous source-drain diode current	T _A = 25 °C	- I _S	3.3 ^{b, c}	ĺ	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	30	1	
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	45	mJ	
	T _C = 25 °C		52		
Movimum newer discinction	T _C = 70 °C		33	w	
Maximum power dissipation	T _A = 25 °C	PD	3.7 ^{b, c}	vv	
	T _A = 70 °C		2.4 ^{b, c}	1	
Operating junction and storage temperature range		TJ, Tstg	-55 to +150	°C	
Soldering recommendations (peak temperature) ^c			260		

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	t ≤ 10 s	R _{thJA}	24	33	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJF}	1.9	2.4	C/W

Notes

a.

Package limited. Surface mounted on 1" x 1" FR4 board. b.

c. t = 10 s

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under steady state conditions is 81 °C/W.

g. T_C = 25 °C.

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Document Number: 75465

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	•
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	25	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 10 mA	-	21	-	
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-4.8	-	mV/°C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	1	-	2.1	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = +20 / -16 V$	-	-	100	nA
Zero gate voltage drain current		$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V, T _J = 70 °C	-	-	15	μA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	40	-	-	Α
Drain source on state registance a		V _{GS} = 10 V, I _D = 15 A	-	0.00115	0.00140	0
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A	-	0.00195	0.00240	Ω
Forward transconductance a	g _{fs}	V _{DS} = 15 V, I _D = 15 A	-	75	-	S
Dynamic ^b					•	•
Input capacitance	C _{iss}		-	2650	-	
Output capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	1015	-	pF
Reverse transfer capacitance	C _{rss}		-	197	-	
Total acto charge	0	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	36.5	55	
Total gate charge	Qg		-	17.2	26	
Gate-source charge	Q _{gs}	V_{DS} = 10 V, V_{GS} = 4.5 V, I_{D} = 15 A	-	7.4	-	nC
Gate-drain charge	Q _{gd}		-	3.3	-	
Gate resistance	R _g	f = 1 MHz	0.2	0.75	1.35	Ω
Turn-on delay time	t _{d(on)}		-	12	24	
Rise time	tr	$V_{DD} = 10 \text{ V}, \text{ R}_{\text{I}} = 1 \Omega, \text{ I}_{\text{D}} \cong 15 \text{ A},$	-	23	46	
Turn-off delay time	t _{d(off)}			18	36	
Fall time	t _f		-	10	20	
Turn-on delay time	t _{d(on)}		-	18	36	ns
Rise time	t _r	$V_{DD} = 10 \text{ V}, \text{ R}_{L} = 1 \Omega, \text{ I}_{D} \cong 15 \text{ A},$	-	42	84	
Turn-off delay time	t _{d(off)}	V_{GEN} = 4.5 V, R_g = 1 Ω	-	17	34	
Fall time	t _f		-	17	34	
Drain-Source Body Diode Characteristi	cs				•	•
Continuous source-drain diode current	IS	T _C = 25 °C	-	-	56.8	•
Pulse diode forward current	I _{SM}		-	-	150	A
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.73	1.1	V
Body diode reverse recovery time	t _{rr}		-	32	64	ns
Body diode reverse recovery charge	Q _{rr}		-	20	40	nC
Reverse recovery fall time	ta	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	-	17	-	
Reverse recovery rise time	t _b		-	15	-	ns

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

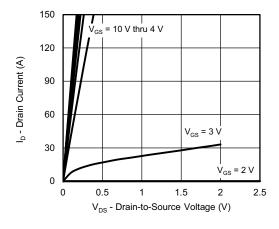
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

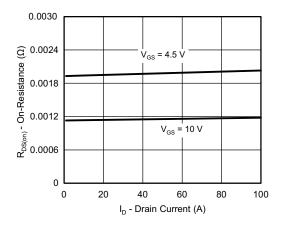


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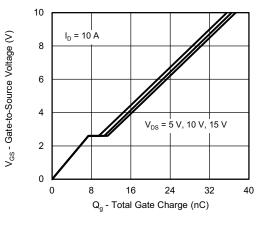
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



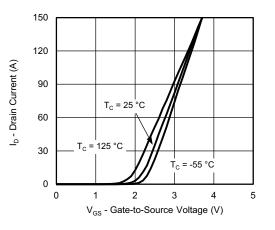
Output Characteristics



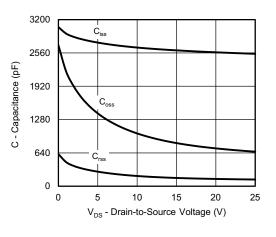
On-Resistance vs. Drain Current and Gate Voltage



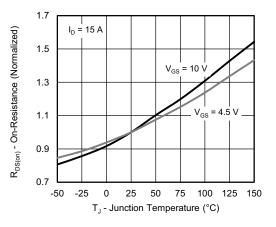
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

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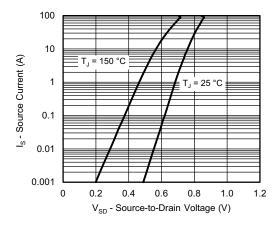
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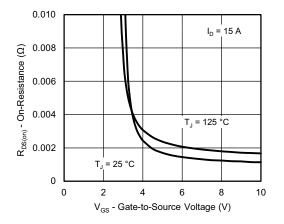


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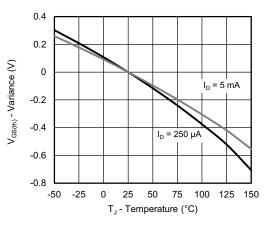
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



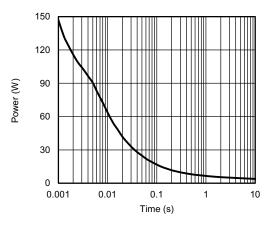
Source-Drain Diode Forward Voltage



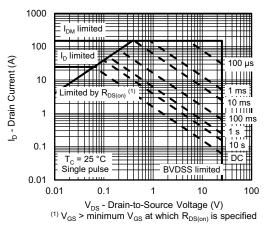
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

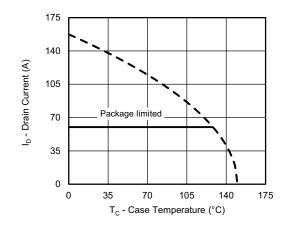
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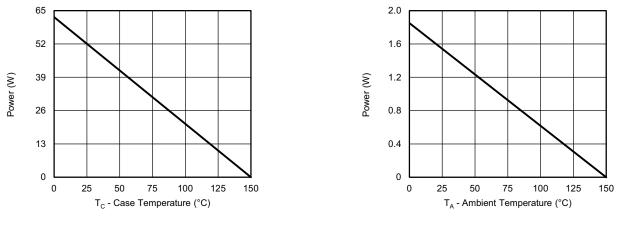
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating a



Power, Junction-to-Case

Power, Junction-to-Ambient

Note

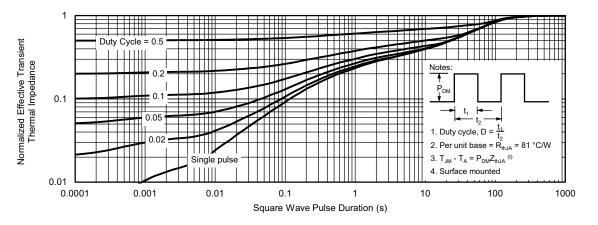
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



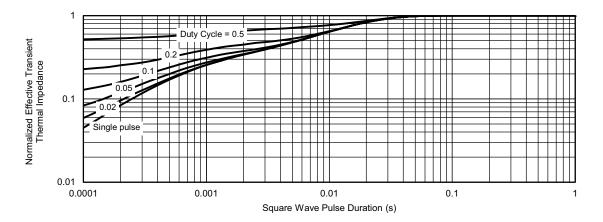
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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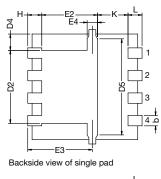


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PowerPAK® 1212-8, (Single / Dual)









Notes

1. Inch will govern

Dimensions exclusive of mold gate burrs
Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES			
DINI.	MIN.	NOM.	MAX.	MIN.	MIN. NOM.		
А	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D3	0.48	-	0.89	0.019	-	0.035	
D4	0.47 typ.				0.0185 typ		
D5		2.3 typ.			0.090 typ		
E	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.034 typ.			0.013 typ.		
е		0.65 BSC		0.026 BSC			
К		0.86 typ.		0.034 typ.			
K1	0.35	-	-	0.014	-	-	
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			
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Revison: 09-Jan-17

Document Number: 71656

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RECOMMENDED MINIMUM PADS FOR PowerPAK[®] 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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